FAIRCHILD

SEMICONDUCTOR

### 74F219 64-Bit Random Access Memory with 3-STATE Outputs

#### **General Description**

The 74F219 is a high-speed 64-bit RAM organized as a 16word by 4-bit array. Address inputs are buffered to minimize loading and are fully decoded on-chip. The outputs are 3-STATE and are in the high-impedance state whenever the Chip Select ( $\overline{CS}$ ) input is HIGH. The outputs are active only in the Read mode. This device is similar to the 74F189 but features non-inverting, rather than inverting, data outputs.

#### **Features**

■ 3-STATE outputs for data bus applications

June 1988

Revised July 1999

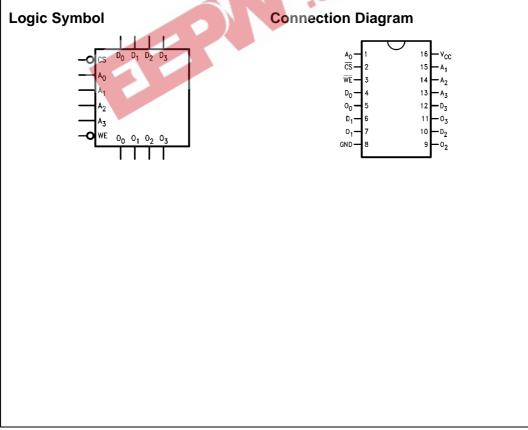
- Buffered inputs minimize loading
- Address decoding on-chip
- Diode clamped inputs minimize ringing

<u>A</u>.

Available in SOIC (300 mil only)

Ordering Code:

Order Number	Package Number	Package Description					
74F219SC	M16B	16-Lead Small Outline Intergrated Circuit (SOIC), JEDEC MS-013, 0.300 Wide					
74F219SJ	M16D	16-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide					
74F219PC	N16E	16-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300 Wide					
Devices also available	Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.						



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74F219 64-Bit Random Access Memory with 3-STATE Outputs

# 74F219

#### Unit Loading/Fan Out U.L. Input I<sub>IH</sub>/I<sub>IL</sub> Pin Names Description Output I<sub>OH</sub>/I<sub>OL</sub> HIGH/LOW Address Inputs 1.0/1.0 20 µA/-0.6 mA $A_0 - A_3$ CS Chip Select Input (Active LOW) 1.0/2.0 $20 \ \mu\text{A/-1.2 mA}$ WE Write Enable Input (Active LOW) 1.0/1.0 $20 \; \mu\text{A/--}0.6 \; \text{mA}$ D<sub>0</sub>-D<sub>3</sub> Data Inputs 1.0/1.0 $20 \; \mu\text{A/--}0.6 \; \text{mA}$ 3-STATE Data Outputs -3 mA/24 mA (20 mA) 150/40 (33.3) O<sub>0</sub>-O<sub>3</sub> **Function Table** Inputs Operation **Condition of Outputs** cs WE High Impedance Write L L L н Read Х Inhibit н H = HIGH Voltage Level L = LOW Voltage Level X = Immaterial **Block Diagram** $D_0$ $D_1$ $D_2$ $D_3$ WE DATA BUFFERS cs Ao 16-WORD × 4-BIT MEMORY CELL Α<sub>1</sub> DECODER DRIVERS ADDRESS DECODER A<sub>2</sub> ARRAY A3 OUTPUT BUFFERS $\circ_0 \circ_1 \circ_2 \circ_3$

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#### Absolute Maximum Ratings(Note 1)

Storage Temperature	$-65^{\circ}C$ to $+150^{\circ}C$
Ambient Temperature under Bias	$-55^{\circ}C$ to $+125^{\circ}C$
Junction Temperature under Bias	$-55^{\circ}C$ to $+150^{\circ}C$
$V_{\mbox{\scriptsize CC}}$ Pin Potential to Ground Pin	-0.5V to +7.0V
Input Voltage (Note 2)	-0.5V to +7.0V
Input Current (Note 2)	-30 mA to +5.0 mA
Voltage Applied to Output	
in HIGH State (with $V_{CC} = 0V$ )	
Standard Output	-0.5V to V <sub>CC</sub>
3-STATE Output	-0.5V to +5.5V
Current Applied to Output	
in LOW State (Max)	twice the rated I <sub>OL</sub> (mA)

## Recommended Operating Conditions

Free Air Ambient Temperature	
Supply Voltage	

74F219

0°C to +70°C +4.5V to +5.5V

Note 1: Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

#### **DC Electrical Characteristics**

Symbol	Parameter		Min	Тур	Max	Units	Vcc	Conditions		
V <sub>IH</sub>	Input HIGH Voltage		2.0			V	J. M	Recognized as a HIGH Signal		
VIL	Input LOW Voltage				0.8	V		Recognized as a LOW Signal		
V <sub>CD</sub>	Input Clamp Diode Voltage				-1.2	V	Min	I <sub>IN</sub> = -18 mA		
V <sub>OH</sub>	Output HIGH	10% V <sub>CC</sub>	2.5		10 13			I <sub>OH</sub> = -1 mA		
	Voltage	10% V <sub>CC</sub>	2.4		122		Min	$I_{OH} = -3 \text{ mA}$		
		5% V <sub>CC</sub>	2.7			O	IVIII	$I_{OH} = -1 \text{ mA}$		
		5% V <sub>CC</sub>	2.7					$I_{OH} = -3 \text{ mA}$		
V <sub>OL</sub>	Output LOW	10% V <sub>CC</sub>			0.5	V	Min	1 04 m 4		
	Voltage				0.5	v	IVIII	$I_{OL} = 24 \text{ mA}$		
I <sub>IH</sub>	Input HIGH				5.0		Maria	N 0.7V		
	Current				5.0	μA	Max	V <sub>IN</sub> = 2.7V		
I <sub>BVI</sub>	Input HIGH Current				7.0		Max	V 70V		
	Breakdown Test				7.0	μA	IVIAX	$V_{IN} = 7.0V$		
I <sub>CEX</sub>	Output HIGH				50	μΑ	Max	N N		
	Leakage Current							$V_{OUT} = V_{CC}$		
V <sub>ID</sub>	Input Leakage		4.75			V	0.0	$I_{ID} = 1.9 \mu A$		
	Test		4.75			v	0.0	All Other Pins Grounded		
I <sub>OD</sub>	Output Leakage				3.75	μA	0.0	$V_{IOD} = 150 \text{ mV}$		
	Circuit Current				3.75	μА	0.0	All Other Pins Grounded		
I <sub>IL</sub>	Input LOW				-0.6	mA	Max	$V_{IN} = 0.5V (A_n, \overline{WE}, D_n)$		
	Current				-1.2			$V_{IN} = 0.5V (\overline{CS})$		
I <sub>OZH</sub>	Output Leakage Current				50	μA	Max	$V_{OUT} = 2.7V$		
I <sub>OZL</sub>	Output Leakage Current				-50	μA	Max	V <sub>OUT</sub> = 0.5V		
los	Output Short-Circuit Current		-60		-150	mA	Max	$V_{OUT} = 0V$		
I <sub>ZZ</sub>	Bus Drainage Test				500	μA	0.0V	V <sub>OUT</sub> = 5.25V		
Icc	Power Supply Current			37	55	mA	Max			

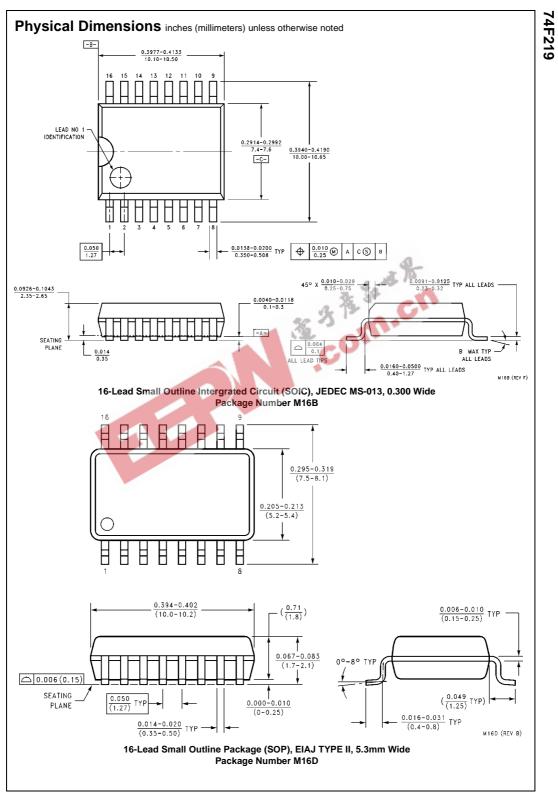
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#### **AC Electrical Characteristics**

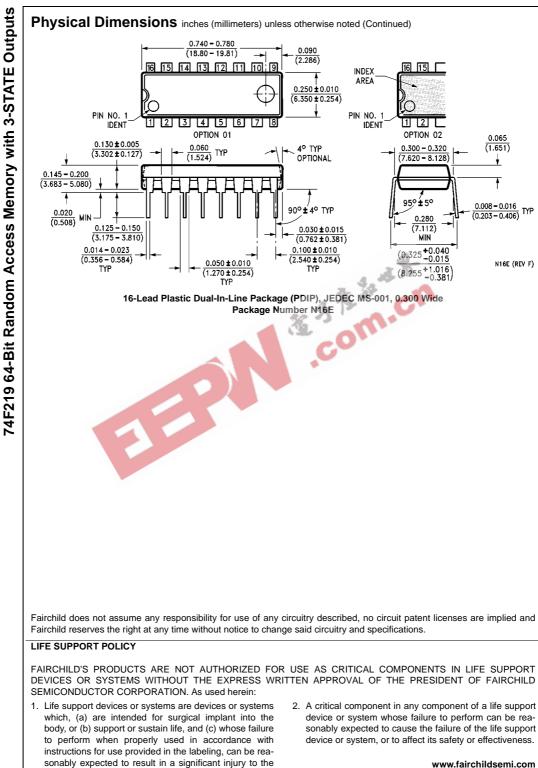
Symbol	Parameter	$T_{A} = +25^{\circ}C$ $V_{CC} = +5.0V$ $C_{L} = 50 \text{ pF}$			$T_A = -55^{\circ}C \text{ to } +125^{\circ}C$ $V_{CC} = +5.0V$ $C_L = 50 \text{ pF}$		$T_{A} = 0^{\circ}C \text{ to } +70^{\circ}C$ $V_{CC} = +5.0V$ $C_{L} = 50 \text{ pF}$		Units
		Min	Тур	Max	Min	Max	Min	Max	
t <sub>PLH</sub>	Access Time, HIGH or LOW	10.0	18.5	26.0	9.0	32.0	10.0	27.0	ns
t <sub>PHL</sub>	A <sub>n</sub> to O <sub>n</sub>	8.0	13.5	19.0	8.0	23.0	8.0	20.0	115
t <sub>PZH</sub>	Access Time, HIGH or LOW	3.5	6.0	8.5	3.5	10.5	3.5	9.5	ns
t <sub>PZL</sub>	CS to On	5.0	9.0	13.0	5.0	15.0	5.0	14.0	
t <sub>PHZ</sub>	Disable Time, HIGH or LOW	2.0	4.0	6.0	2.0	8.0	2.0	7.0	
t <sub>PLZ</sub>	CS to On	3.0	5.5	8.0	2.5	10.0	3.0	9.0	
t <sub>PZH</sub>	Write Recovery Time	6.5	20.0	28.0	6.5	37.5	6.5	29.0	ns
t <sub>PZL</sub>	HIGH or LOW, WE to On	6.5	11.0	15.5	6.5	17.5	6.5	16.5	
t <sub>PHZ</sub>	Disable Time, HIGH or LOW	4.0	7.0	10.0	3.5	12.0	4.0	11.0	
t <sub>PLZ</sub>	WE to On	5.0	9.0	13.0	5.0	15.0	5.0	14.0	

#### **AC Operating Requirements**

		$T_A = +25^{\circ}C$		$T_A = -55^{\circ}C \text{ to } +125^{\circ}C$		$T_A = 0^{\circ}C \text{ to } +70^{\circ}C$		
Symbol	Parameter	Vcc	c = +5.0V	V <sub>CC</sub> = +5.0V		V <sub>CC</sub> = +5.0V		Units
		Min	Max	Min	Max	Min	Max	
t <sub>S</sub> (H)	Setup Time, HIGH or LOW	0	38 3	0		0		ns
t <sub>S</sub> (L)	A <sub>n</sub> to WE	0	132	0		0		
t <sub>H</sub> (H)	Hold Time, HIGH or LOW	2.0	C	2.0		2.0		
t <sub>H</sub> (L)	A <sub>n</sub> to WE	2.0		2.0		2.0		
t <sub>S</sub> (H)	Setup Time, HIGH or LOW	10.0		11.0		10.0		ns
t <sub>S</sub> (L)	D <sub>n</sub> to WE	10.0		11.0		10.0		
t <sub>H</sub> (H)	Hold Time, HIGH or LOW	0	-	2.0		0		
t <sub>H</sub> (L)	$D_n$ to $\overline{WE}$	0		2.0		0		
t <sub>S</sub> (L)	Setup Time, LOW	0		0		0		ns
	CS to WE							
t <sub>H</sub> (L)	Hold Time, LOW	6.0		7.5		6.0		
	CS to WE							
t <sub>W</sub> (L)	WE Pulse Width, LOW	6.0		15.0		6.0		ns



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